

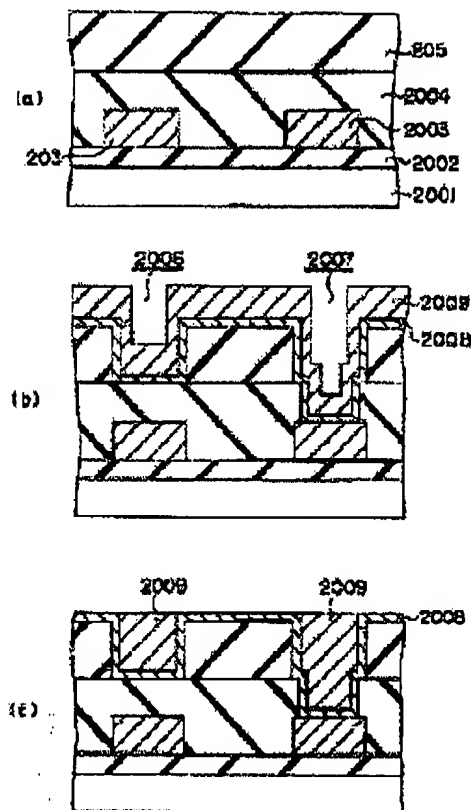
## SEMICONDUCTOR DEVICE AND MANUFACTURE THEREOF

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- **international:** H01L21/3205; H01L21/768  
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### Abstract of JP9064034

**PROBLEM TO BE SOLVED:** To obtain a semiconductor device effective for using interconnection materials such as Au, Ag, Cu by providing an insulating film formed on a first electrode or interconnection layer made of Al and a second electrode or interconnection layer made of metal having lower specific resistance and melting point than those of the Al thereon. **SOLUTION:** The semiconductor device comprises a semiconductor substrate 2001 formed with a semiconductor element, a first insulating film 2002 formed on the substrate 2001, and first electrode or interconnection layers 203, 2003 made of Al formed on the film 2002. Further, the device comprises a second insulating film 2004 formed on the electrode or interconnection 203, 2003, and a second electrode or interconnection layer 2009 made of metal having lower specific resistance and melting point than those of the Al formed on the film 2004. For example, the metal is Au, Ag or Cu, and a protective film 2008 without reaction with the metal and preventing the diffusion of the metal is provided at least in the bottom of the layer 2009.



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